

SILICON MOS N-CHANNEL POWER TRANSISTOR 300 W, up to 230 MHz, Enhancement Mode

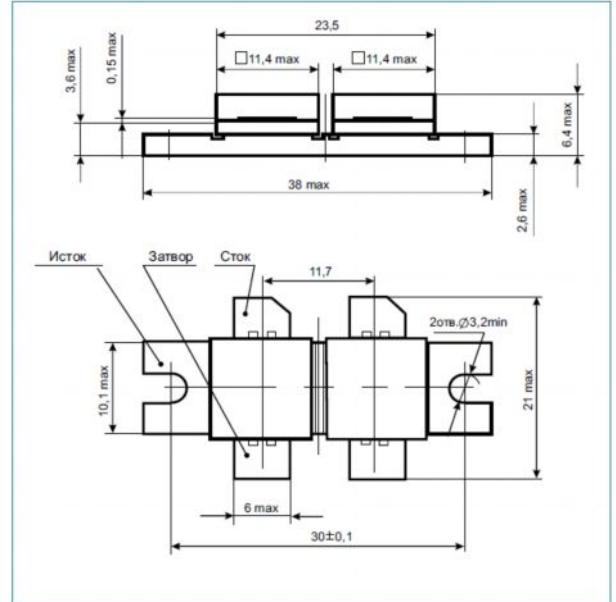
The silicon MOS transistor is designed for professional transmitter applications in the HF/VHF frequency range.

Features:

- Performance at 230 MHz, 28 Vdc
- Power Gain: 10 dB Min
- Output Power: 300 W
- Efficiency: 50 % Min

Absolute Maximum Ratings

Parameters	Sym	Value	Unit
Drain-Source Voltage	V_{DS}	65	V_{DC}
Drain Current-Continuous	I_D	40	A_{DC}
Gate-Source Voltage	V_{GS}	± 20	V_{DC}
Operation Junction Temperature	T_j	$-65 \div +200$	$^{\circ}C$
Storage Temperature Range	T_{STG}	$-65 \div +150$	$^{\circ}C$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.4	$^{\circ}C/W$
Total Power Dissipation	P_D	438	W



Case KT-82

Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage ($I_{DS}=50$ mA, $V_{GS}=0$ V)	$V_{(BR)DSS}$	65	—	—	V_{DC}
Gate-Source Leakage Current ($V_{GS}=20$ V, $V_{DS}=0$ V)	I_{GSS}	—	—	1	μA_{DC}
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28$ V, $V_{GS}=0$ V)	I_{DSS}	—	—	20	mA_{DC}
Gate Threshold Voltage ($V_{DS} = 10$ V, $I_D = 100$ mA)	$V_{GS(TH)}$	2	—	5	V_{DC}
Forward Transconductance ($V_{DS} = 10$ V, $I_D = 5$ A) (1)	G_{FS}	4	5	—	mhos
Input Capacitance ($V_{DS} = 28$ V, $V_{GS}=0$ V, $f = 1$ MHz) (1)	C_{ISS}	—	530	—	pF
Output Capacitance ($V_{DS} = 28$ V, $V_{GS}=0$ V, $f = 1$ MHz) (1)	C_{OSS}	—	310	—	pF
Reverse Transfer Capacitance ($V_{DS} = 28$ V, $V_{GS}=0$ V, $f = 1$ MHz) (1)	C_{RSS}	—	35	—	pF
Power Gain ($V_{DS} = 28$ V, $P_{OUT} = 300$ W, $I_{DQ.} = 100$ mA, $f = 230$ MHz)	Gp	10	11.5	—	dB
Drain Efficiency ($V_{DS} = 28$ V, $P_{OUT} = 300$ W, $I_{DQ.} = 100$ mA, $f = 230$ MHz)	η_D	50	60	—	%

(1) Each transistor chip measured separately.

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Specification is subject to change without notice